



## austriamicrosystems 0.8 $\mu\text{m}$ CMOS (CXZ)

### Technology Description

#### Mixed Analog/Digital Process/High Voltage

- The 0.8 $\mu\text{m}$  CMOS technology is a mixed mode process with two layers of metal and a high resistive poly.
- Operating Voltage [V]: 2.5-50

#### General Characteristics

- p substrate
- pseudo twin-well CMOS

#### Layout Rules

- Minimum electrical gate length : 0.8  $\mu\text{m}$  for both PMOS and NMOS
- Polysilicon pitch : 1.7  $\mu\text{m}$
- Metal 1 pitch : 2.1 $\mu\text{m}$
- Metal 2 pitch : 2.3 $\mu\text{m}$

#### Thin Oxide Poly/Poly Capacitor

- Double poly capacitor
- High value : 0.86 fF/ $\mu\text{m}^2$
- High resistive Poly: 1.2 kOhm/square

### Standard Cell Libraries

#### Digital Library

- Characterised at 5 V and 3.3 V operation
- Core cells optimized for synthesis
- I/O cells (pad and core limited)
- Maximum Junction temperature 150 deg C
- VHDL/Vital

#### Analog Library

- Not available through EUROPRACTICE.
- Available directly from austriamicrosystems. EUROPRACTICE can provide the contact address.